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Appl. No. 10/710901

Applicant : Rong Huang  
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Title : Thermally Tunable Laser with Single Solid Etalon  
Wavelength Locker

Honorable Commissioner for Patents  
Alexandria, VA 22313

### AMENDMENT

Sir:

I found a few writing irregularities in the claims and I want to make some reorganizations of the claims, please amend the above-identified application as follows:

[claim 1] A wavelength locked thermally tunable laser comprising:

A semiconductor laser, whose output wavelength adjusted thermally and continuously;

A wavelength locker, comprising:

- (a) a solid etalon, whose free space range or its physical thickness relates to the temperature characteristics of said semiconductor laser;
- (b) a first photo detector for detecting a collimated light extracted from said semiconductor laser and transmitting through said solid etalon;
- (c) a second photo detector for detecting the power output of said semiconductor laser;

Said semiconductor laser and wavelength locker packaged on one single platform;

The temperature of said platform, semiconductor laser and solid etalon adjusted by a thermal electrical cooler;

A temperature detecting element disposed near said solid etalon for detecting the ambient temperature of said etalon;

A means of locking the wavelength of said semiconductor laser to a specific wavelength by an outside electronic controller.

[claim 2] A wavelength locked thermally tunable laser of claim 1 wherein said solid etalon having a free spectrum range FSR or physical thickness  $t(T)$  at a temperature  $T$  is defined by a first partial reflector and a second partial reflector, said reflectors formed on the two parallel surfaces of a piece of transparent material.

[claim 3] The solid etalon of claim 2 wherein the FSR of said solid etalon

$$FSR = \Delta \nu - \frac{\Delta \nu}{(d\nu/dT)_{laser}} \times (d\nu/dT)_{etalon},$$

where  $\Delta \nu$  is the channel spacing, such as 100GHz, 50GHz etc.;  $(d\nu/dT)_{laser}$  the temperature dependence of the emission frequency of said semiconductor laser; and  $(d\nu/dT)_{etalon}$  the temperature dependence of said solid etalon's resonance peak frequency.

[claim 4] The solid etalon of claim 2 wherein the physical thickness  $t(T)$  of said solid etalon

$$t(T_1) = \frac{L\lambda_1\lambda_2 + 2n(\lambda_2, T_2)\alpha\Delta T\lambda_1}{2n(\lambda_1, T_1)\lambda_2 - 2n(\lambda_2, T_2)\lambda_1},$$

where  $\lambda_1$  is the output wavelength at temperature  $T_1$  of said semiconductor laser;  $\Delta\lambda$  is the channel spacing corresponding to 100GHz, 50GHz, etc.;  $\lambda_2 = \lambda_1 + L\Delta\lambda$  is the output wavelength at  $T_2$  of said semiconductor laser;  $\alpha$  is the thermal expansion coefficient of the material of said solid etalon;  $L$  is an integer (=1, 2, ...);  $\Delta T = T_2 - T_1$  is the temperature change required to change the output wavelength from  $\lambda_1$  to  $\lambda_2$  of said semiconductor laser;  $n(\lambda_1, T_1)$  and  $n(\lambda_2, T_2)$  are the refractive index of the material of said solid etalon at  $\lambda_1, T_1$  and  $\lambda_2, T_2$ , respectively.

[claim 5] The wavelength locked thermally tunable laser of claim 1, further comprising a means to adjust a locking point value set at temperature  $T$  and wavelength  $\lambda$  according to a measured temperature  $T'$  by an amount of  $[I(\lambda, T') - I(\lambda, T)]$ , where  $I(\lambda, T)$  is the normalized (against the power fluctuation) transmission intensity of said solid etalon at the locking wavelength  $\lambda$  and the temperature  $T$  and  $I(\lambda, T')$  is the normalized transmission intensity of said solid etalon at the locking wavelength  $\lambda$  and temperature  $T'$ .